

# Atomistic Kinetic Monte Carlo Simulations of Polycrystalline Copper Electrodeposition

Tanyakarn Treeratanaphitak<sup>a</sup>, Mark D. Pritzker<sup>a</sup>, Nasser Mohieddin Abukhdeir<sup>a,b,\*</sup>

<sup>a</sup>Department of Chemical Engineering

<sup>b</sup>Waterloo Institute for Nanotechnology

University of Waterloo

200 University Avenue West

Waterloo, Ontario, Canada N2L 3G1

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## Abstract

A high-fidelity kinetic Monte Carlo (KMC) simulation method (T. Treeratanaphitak, M. Pritzker, N. M. Abukhdeir, *Electrochim. Acta* 121 (2014) 407–414) using the semi-empirical multi-body embedded-atom method (EAM) potential has been extended to model polycrystalline metal electrodeposition. The presented KMC-EAM method enables true three-dimensional atomistic simulations of electrodeposition over experimentally relevant timescales. Simulations using KMC-EAM are performed over a range of overpotentials to predict the effect on deposit texture evolution. Results show strong agreement with past experimental results both with respect to deposition rates on various copper surfaces and roughness-time power law behaviour. It is found that roughness scales with time  $\propto t^\beta$  where  $\beta = 0.62 \pm 0.12$ , which is in good agreement with past experimental results. Furthermore, the simulations provide insights into sub-surface deposit morphologies which are not directly accessible from experimental measurements.

**Keywords:** electrodeposition, simulation, kinetic Monte Carlo, embedded atom method, polycrystalline

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## 1. Introduction

Electrodeposition is widely used to fabricate micro- and nano-structures for various applications including interconnects [1], electrodes [2], catalysts and sensors [3]. The preferred deposit morphology that yields optimal performance varies depending on the application. Thus, it is important to better understand the fundamental processes occurring during electrodeposition and the complex relationship between process parameters and growth kinetics.

Atomistic simulations of electrodeposition can help predict the relationship between process parameters and kinetics. These simulations can be used to enhance and focus experimental research through identification of key processes and parameter regimes. Kinetic Monte Carlo (KMC) methods are an important class of simulation methods capable of modelling the dynamics of electrodeposition at experimentally-relevant time scales. Until recently, KMC simulations have been limited to using models of deposits which do not directly relate to atomistic morphology. Recent advances [4–6] in high-fidelity atomistic KMC simulations using the highly descriptive embedded-atom method (EAM) potential [7, 8] have moved the state-of-the-art closer to being able to make direct comparisons with experimental data from electrodeposition processes.

The traditional approach to KMC simulation of polycrystalline deposition is to use the so-called “1+1” dimension solid-on-solid model (SOS) [9]. The SOS approach, while computationally efficient, has several limitations when comparing simulated morphologies to atom-resolution deposits and in the severe approximations made regarding deposit energetics [4]. Instead of computing the energy of the deposit from an interaction potential, the SOS method treats the energy at each site as a sum of two terms that scale linearly as a function of coordination number. Bruschi et

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\*Corresponding author. Phone: +1 (519) 888-4567 x31306

Email addresses: pritzker@uwaterloo.ca (Mark D. Pritzker), nmabukhdeir@uwaterloo.ca (Nasser Mohieddin Abukhdeir)

URL: <http://chemeng.uwaterloo.ca/abukhdeir/> (Nasser Mohieddin Abukhdeir)

al. [10] developed a two-dimensional KMC method for polycrystalline thin film deposition. This approach is limited to sub-monolayer growth since it captures the behaviour of the system only in the  $x$  and  $y$  directions. Liu et al. [11, 12] developed a two-dimensional cross-sectional ( $x-z$  plane) polycrystalline KMC method to model the electrodeposition of copper onto copper and gold with an arbitrary “strange” coordination number to account for the interaction across grains.

In a recent advance, Huang et al. [6] simulated nickel electrodeposition under kinetically-controlled conditions in the presence of hydrogen atoms, although limited to two-dimensional simulation. This method used a high-fidelity atomistic resolution of the deposit and the EAM potential to describe the Ni-Ni and Ni-H interatomic interactions. Three-dimensional polycrystalline simulation using KMC and the EAM potential was performed for vapour deposition by Gilmer et al [13, 14]. This work was limited to evaluation of the deposit energy using only first nearest neighbours, which does not completely describe the potential energy of the atoms using EAM. Polycrystallinity was captured by assigning orientation angles to sites, but restricting their positions to a single lattice. Rubio et al. [15] extended the model to represent the polycrystalline structure with multiple lattices but still retained the assumption that the potential is only a function of first nearest neighbours. This restriction on the interaction potential can influence the deposit morphology obtained from simulations. In addition, existing three-dimensional KMC methods were not developed for electrodeposition and thus cannot capture the effect of electrochemical kinetics (both deposition and dissolution) on the deposit morphology.

In this work, a KMC method is presented and used to simulate polycrystalline electrodeposition using the multi-body EAM potential (KMC-EAM) which includes collective diffusion mechanisms, deposition and dissolution mechanisms and direct resolution of atomic polycrystalline morphologies. The KMC-EAM method is applied to three-dimensional potentiostatic copper electrodeposition onto an atomically smooth polycrystalline copper substrate. In addition, the spatially varying deposition and dissolution rates are obtained from the difference in surface energies of the crystal faces that are exposed. The simulations are conducted to model potentiostatic deposition over a range of experimentally-relevant overpotentials and determine the resulting evolution of roughness and deposition rate.

## 2. Model Description

The presented polycrystalline KMC-EAM method is an extension of the single-crystal KMC-EAM method from ref. [4] and is applied to describe potentiostatic deposition of copper. The KMC-EAM method is a three-dimensional kinetic Monte Carlo method that uses a direct atomistic representation of a metal deposit. The total energy or Hamiltonian is resolved using the highly descriptive EAM interaction potential which is fit to quantum mechanical simulations and experimental results such as lattice constant, elastic constant and sublimation energy [7]. The specific EAM parameters used for copper are obtained from ref. [8]. Another unique aspect of the KMC-EAM method is that it includes collective diffusion mechanisms such as atom exchange and step-edge atom exchange, which have been shown to be vital to accurately simulate single-crystal deposition morphology [4].

The extension of KMC-EAM to polycrystalline electrodeposition requires modelling atomic configurations where metal atoms can occupy different crystal lattices. Since the EAM potential does not require that atoms reside on a fixed lattice, evaluation of the energy of the system requires no modifications to the potential. For this study, nucleation is neglected and an atomically smooth polycrystalline copper (FCC) deposit is used as the initial condition to replicate the deposition onto a polished substrate. Each grain resides on a different lattice of arbitrary (user-selected) orientation, which is set as an initial condition. During simulation, electrodeposition occurs only on grain surfaces that are exposed while collective diffusion mechanisms are permitted on all grain surfaces. When grain boundaries are in close proximity to each other, mutual grain growth on unoccupied sites within an impingement distance of  $a\sqrt{2}/2$  is inhibited, where  $a$  is the lattice spacing. Additionally, the rates of both deposition and dissolution are not uniform across the surface and depend on the surface energy of the exposed grain crystal face. The surface energy computed from the embedded-atom method does not take into account interactions with the electrolyte and, as a result, approximations which conform to the macroscopic deposition/dissolution rates are used. These approximations involve linearization of the propensity about the average change in energy resulting from deposition/dissolution computed from the EAM

potential; the resulting propensities ( $\Gamma_i$ ) at each site are:

$$\Gamma_{i,dep} = \frac{i_{Cu}^0}{z e n_{dep}} \exp\left(-\frac{\alpha_c \eta}{k_B T}\right) \frac{\Delta^\downarrow E_i}{\Delta^\downarrow E_{avg}}, \quad (1)$$

$$\Gamma_{i,diss} = \frac{i_{Cu}^0}{z e n_{diss}} \exp\left(\frac{\alpha_a \eta}{k_B T}\right) \left(2 - \frac{\Delta^\uparrow E_i}{\Delta^\uparrow E_{avg}}\right), \quad (2)$$

where  $i_{Cu}^0$  is the exchange current density ( $A m^{-2}$ ),  $\alpha_a/\alpha_c$  is the anodic/ cathodic transfer coefficients,  $\eta$  is the overpotential (V),  $n_{dep}/n_{diss}$  is the number of sites per surface area ( $m^{-2}$ ) available for deposition/dissolution,  $\Delta^\downarrow E_{avg}/\Delta^\uparrow E_{avg}$  is the average energy difference over all possible deposition/dissolution events and  $\Delta^\downarrow E_i/\Delta^\uparrow E_i$  is the difference in energy before and after deposition/dissolution at site  $i$  (eV). The current density is calculated from the Butler-Volmer equation at the specified overpotential using parameters from ref. [16].

Propensity of diffusion events follow an Arrhenius-type relationship [4]:

$$\Gamma_{i,d} = \begin{cases} \nu_d \exp\left(-\frac{E_d}{k_B T}\right) & \Delta E \leq 0 \\ \nu_d \exp\left(-\frac{E_d + \Delta E}{k_B T}\right) & \Delta E > 0 \end{cases} \quad (3)$$

where  $E_d$  is the activation energy (eV) of one of the following diffusion events: hopping, atom exchange, step-edge atom exchange or grain boundary diffusion. While activation energies of diffusion could be computed using the EAM potential [17], this procedure is computationally prohibitive and thus previously computed values are used instead. The activation energy of grain boundary diffusion is assumed to be 0.5 eV while the other activation energies are the same as those used in the previous single-crystal study [4]:  $E_{hopping} = 0.5$  eV,  $E_{step} = 0.2$  eV and  $E_{exch} = 0.7$  eV [17].

Periodic boundary conditions are used at the domain boundaries along  $x$ - and  $y$ -axes to approximate bulk surface deposition and electrodeposition occurs on exposed surfaces. Copper reduction is assumed to proceed by a one-step reaction under conditions where it is kinetically controlled, i.e., mass transfer from the electrolyte plays no role. All simulations are performed for deposition of a given number of atoms ( $7 \times 10^4$ ) within a simulation domain of  $3023 \text{ nm}^3$  at different experimentally-relevant overpotentials.

### 3. Results and Discussion

Figures 1a-d show the simulated evolution of a deposit from an initially smooth condition when  $\eta = -0.15$  V. The process occurs over a timescale of  $\approx 1$  s (depending on the overpotential), starting from an initial condition (Figure 1a) chosen to contain three FCC surface orientations: (100), (111) and (110). Figures 1b-d exhibit the general trends observed in all simulations which reveal that the (111) surface grows at a faster rate than the other surfaces. Additionally, the (111) grains exhibit three-dimensional growth while the (100) grains exhibit primarily layer-by-layer two-dimensional growth. Figures 2a-c show cross-sections of final deposit morphologies obtained from three different simulations conducted at different  $\eta$ . These figures more clearly show the differences in grain growth among different surface orientations and that the (110) surface morphology is intermediate to that of the other two orientations. These observed trends are in agreement with experimental observations of Cu/Cu(100) and Cu/Cu(111) homoepitaxy [18, 19].

The evolution of the root-mean-squared roughness ( $R_{RMS}$ ) is computed for simulations with three overpotentials (Figure 3a). Roughness evolution is found to obey a power law relationship  $R_{RMS} = C t^\beta$  where  $C$  depends on overpotential while the exponent  $\beta = 0.62 \pm 0.12$  is independent of it over the range considered. The value of  $\beta$  obtained from the KMC-EAM simulations is in good agreement with experimental results obtained for copper electroplating ( $\beta = 0.45 \pm 0.05$  [20]), copper sputtering ( $\beta = 0.62 \pm 0.07$  [21]) and copper electroplating onto single-crystal Cu(111) ( $\beta = 0.51$  [22]). Compared to past simulation results using the standard SOS model where  $\beta = 0.04 \pm 0.06$  was obtained [22], the presented results show significantly better agreement with experiments.

Finally, Figure 3b shows the evolution of the sub-surface of the deposit, which is inaccessible using current experimental methods. From the results for  $\eta = -0.15$  V, the total volume of the (111) grain grows faster than the other two surface orientations. This is supported by past findings that the (111) orientation has the lowest surface energy [23, 24] which is accounted for in the KMC-EAM method through Eqn (1).

## 4. Conclusions

The KMC-EAM methodology has been extended from simulation of single-crystal to polycrystalline electrodeposition. This includes capturing arbitrarily many grain orientations and the inclusion of additional mechanisms including atom dissolution and grain boundary diffusion. Electrodeposition simulations are performed at an atomistic level and results show preferential growth of the (111) orientation in agreement with the experimental observations. Additionally, observed growth modes are in agreement with experimental results for Cu/Cu(100) and Cu/Cu(111) homoepitaxy. Finally, the presented KMC-EAM method is found, for the first time, to predict roughness-time power law behaviour in agreement with experimental studies. These results support the use of the KMC-EAM method for determining experimentally-relevant relationships between surface and sub-surface deposit morphology.

## Acknowledgments

This research was supported by the Natural Sciences and Engineering Research Council (NSERC) of Canada and the facilities of the Shared Hierarchical Academic Research Computing Network (SHARCNET).

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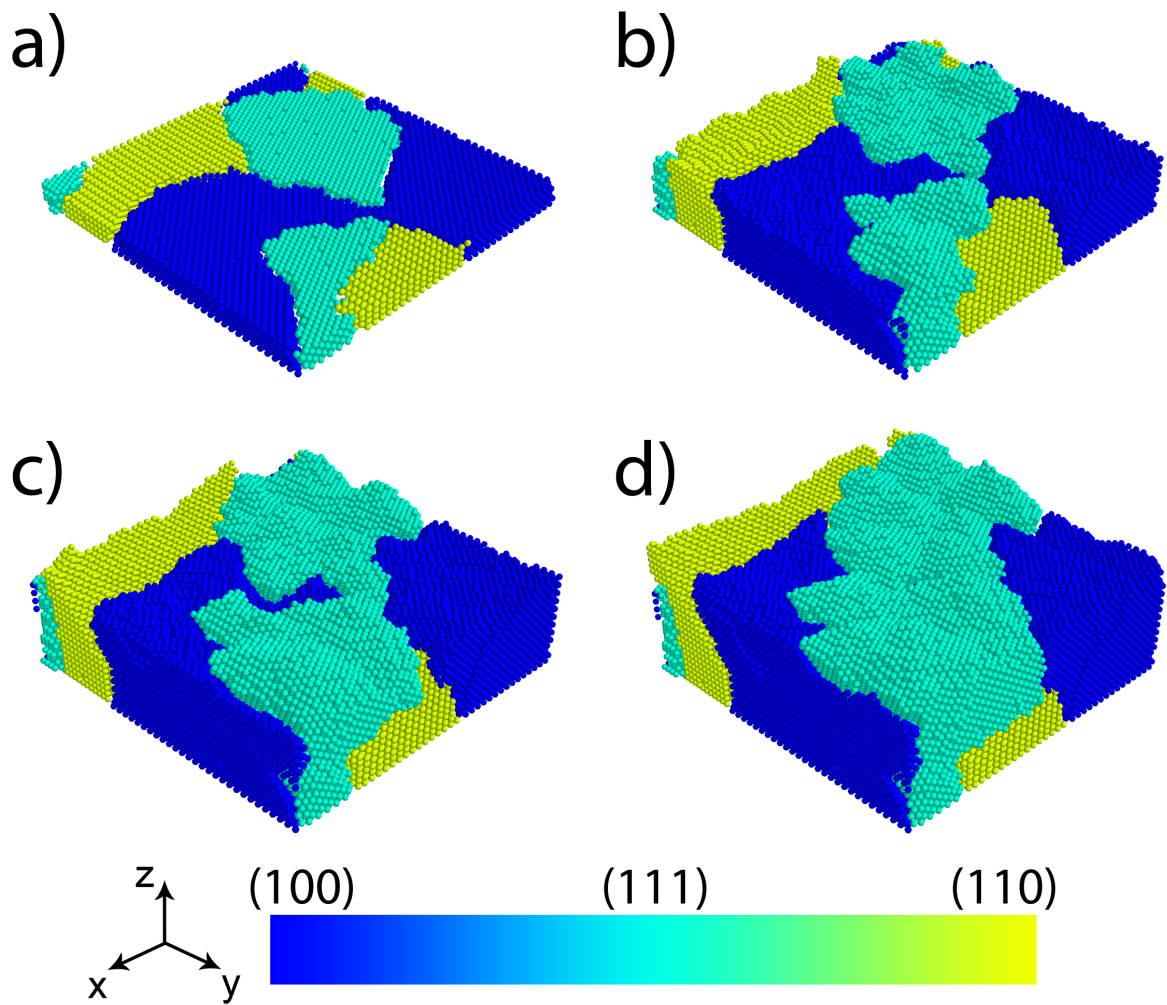


Figure 1: Simulated evolution of an electrodeposit after a) 0% ( $t = 0$  s), b) 33.3% ( $t = 0.05$  s), c) 66.7% ( $t = 0.09$  s) and d) 100% ( $t = 0.13$  s) of the 70000 atoms have been deposited at  $\eta = -0.15$  V.

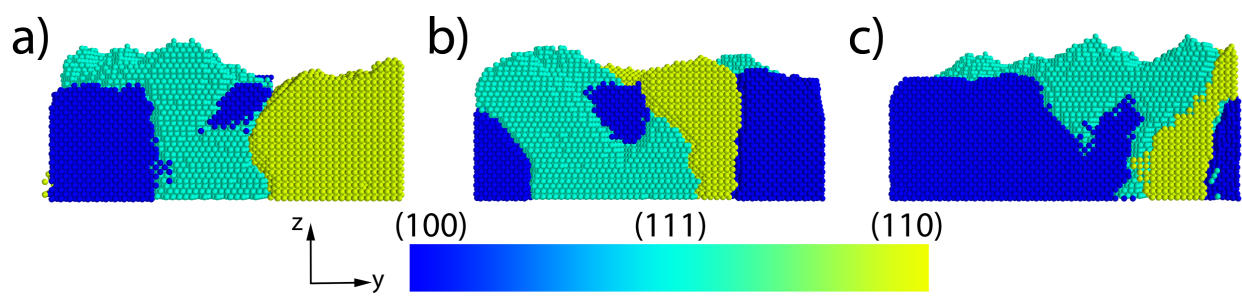


Figure 2: Cross-section view of simulated deposit morphologies at a)  $\eta = -0.05$  V, b)  $\eta = -0.10$  V and c)  $\eta = -0.15$  V.

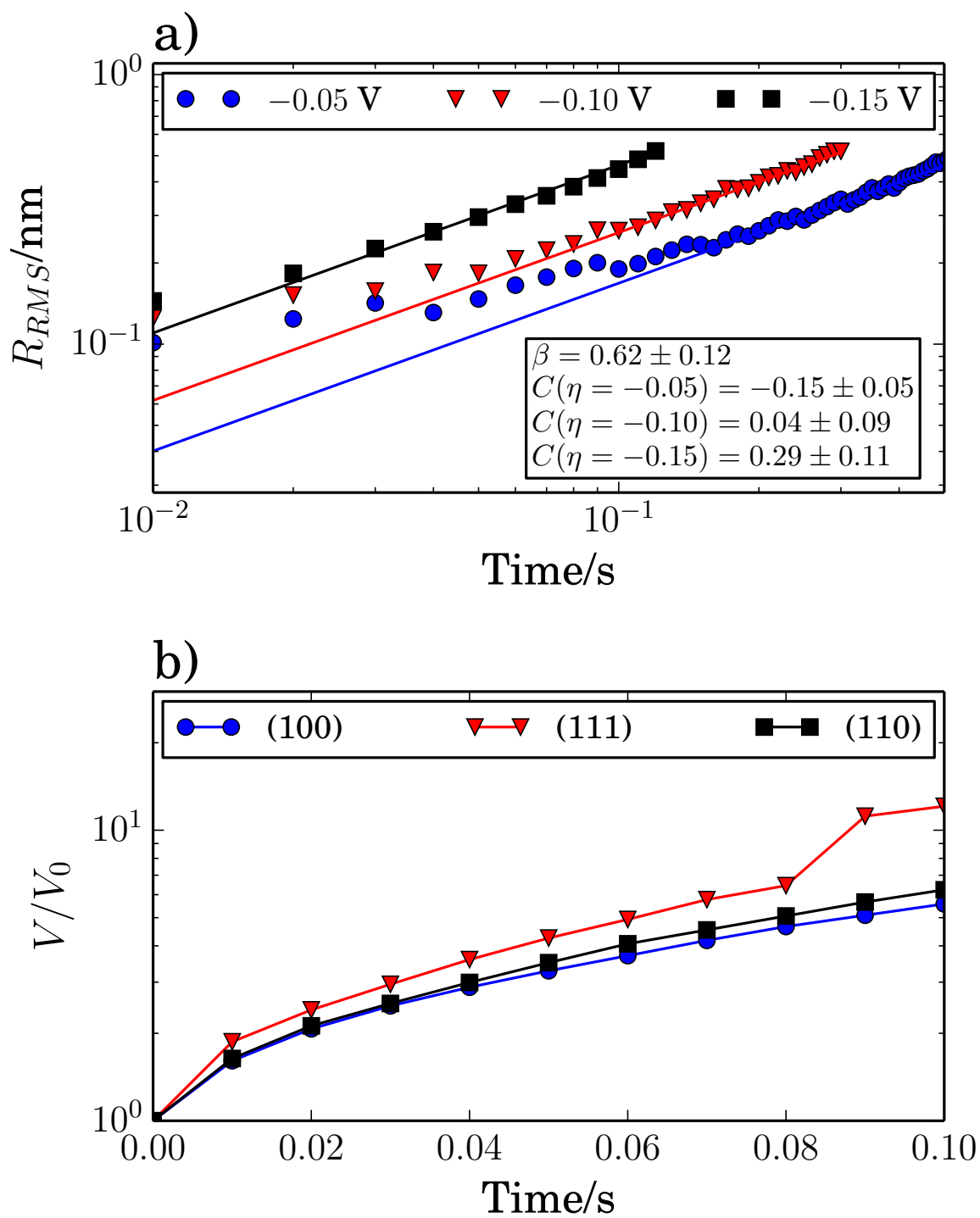


Figure 3: Evolution of a) RMS roughness versus time with power law fit  $R_{RMS} = C(\eta)t^\beta$ ; b) ratio of grain volume over initial volume of the (100), (111) and (110) orientations with time at  $\eta = -0.15$  V.